

TSMC-01-603



February 25, 2002

1765 #2  
13T  
03-25-02  
**RECEIVED**  
MAR 13 2002  
TC 1700

To: Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572  
20 McIntosh Drive  
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/043,863 01/10/02

Chung-Liang Chang et al.

IMPROVEMENT OF PHOTORESIST SCUM FOR  
COPPER DUAL DAMASCENE PROCESS

Grp. Art Unit: 1765

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56. Copies of each document is included herewith.

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner of Patents and  
Trademarks, Washington, D.C. 20231, on March / , 2002.

Stephen B. Ackerman, Reg.# 37761

Signature/Date Stephen B Ackerman 3/1/02

U.S. Patent 6,025,259 to Yu et al., "Dual Damascene Process Using High Selectivity Boundary Layers," discloses a photoresist scum in dual damascene process.

U.S. Patent 5,547,642 to Seiwa et al., "Light Ozone Asher, Light Ashing Method, and Manufacturing Method of Semiconductor Device," discloses a photoresist scum removal process.

U.S. Patent 6,228,755 to Kusumi et al., "Semiconductor Device, and Manufacturing Method Therefor," discloses a dual damascene process.

U.S. Patent 6,074,941 to Hsieh et al., "Method of Forming a Via with Plasma Treatment of SOG," discloses a poison via and plasma treatment process.

U.S. Patent 5,643,407 to Chang, "Solving the Poison Via Problem by Adding N2 Plasma Treatment After Via Etching," discloses a poison via and bake treatment process.

Sincerely,

  
Stephen B. Ackerman,  
Reg. No. 37761